

**LIST OF PRIOR ART
CITED BY APPLICANT**

(Use several sheets if necessary)

Atty. Docket No.
YOR920010308US3 (16315B)

Serial N .
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Applicant
Jack O. Chu, et al.

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL*		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (if appropriate)
<i>[initials]</i>	AA	5,906,680	5/25/1999	Meyerson			
<i>[initials]</i>	AB	6,190,975	2/2001	Kubo et al			
<i>[initials]</i>		2001/0160605	10/2002	Kanazawa et al.;			
<i>[initials]</i>		5,683,934	11/1997	Candelaria et al			
<i>[initials]</i>		2002/0016085	2/2002	Huang et al			
<i>[initials]</i>		6,306,211	10/2001	Takahashi et al.			

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

		E. Kasper, et al. "Growth of 100 Ghz SiGe-Heterobipolar Transistor (HBT) Structures," Jpn J App Phys, Vol. 33 Pt. 1, No. 4B, April 1994, pp. 2415-2418; <i>not provided (see ...)</i>
<i>[initials]</i>		H.J. Osten et al. " in the paper entitled "Carbon Doped SiGe Heterojunction Bipolar Transistors for High Frequency Application," IEEE BCTM 7.1, 1999, pp. 109-116;

EXAMINER *J. Mondt* *[signature]*

DATE CONSIDERED *4/29/05*

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.